

Total No. of printed pages = 7

END SEMESTER EXAMINATION, NOVEMBER 2018

Semester – 3rd (New)

Subject Code : Et-305

ANALOG ELECTRONICS – I

Full Marks – 70

Time – Three hours

The figures in the margin indicate full marks for the questions.

PART – A

Marks – 25

All questions are compulsory.

1. Fill in the blanks :

1 × 10 = 10

- (a) An atom consists of a ——— charged nucleus.
- (b) Electrons in the larger orbits have ——— energy.
- (c) LDR stands for ——— .

[Turn over

- (d) The forward resistance of diode is _____ than its reverse resistance.
 - (e) In a transistor base is very _____ doped.
 - (f) The most commonly used transistor circuit arrangement is _____.
 - (g) Clipping circuits limits the _____ of a output circuit.
 - (h) Clamping circuits can move the _____ signal up or down.
 - (i) The best method of transistor biasing is _____.
 - (j) A single stage transistor amplifier contains _____ transistor.
2. State true or false : $1 \times 10 = 10$
- (a) Energy bands and energy levels are the same.
 - (b) Doping semiconductors with pentavalent impurities produces p type semiconductors.
 - (c) Efficiency of a full wave rectifier is 40.6%.

- (d) A properly doped crystal diode with sharp breakdown voltage is known as Zener diode.
 - (e) A transistor has one pn junction.
 - (f) If the operating point changes unfaithful amplification results.
 - (g) The final stage of a multistage amplifier uses transformer coupling.
 - (h) Semiconductor devices are not sensitive to temperature variations.
 - (i) Class C power amplifier has the highest collector efficiency.
 - (j) A FET is a unipolar transistor.
3. Select the correct answer : $1 \times 5 = 5$
- (a) A Zener diode is operated in
 - (i) Forward region
 - (ii) Rectifier region
 - (iii) Breakdown region
 - (iv) Saturated region.

(b) The number of terminals in a transistor are

- (i) Two
- (ii) Three
- (iii) Five
- (iv) None of the above.

(c) Frequency response is best in the

- (i) Transformer coupled amplifier
- (ii) RC coupled amplifier
- (iii) Oscillators
- (iv) None of the above.

(d) The noise level in a FET compared to a ordinary transistor is

- (i) more
- (ii) no noise at all
- (iii) less
- (iv) None of the above.

38/Et-305/AE-1 (4)

(c) The number of pn junctions in a UJT are

- (i) Three
- (ii) One
- (iii) Two
- (iv) None of the above.

PART - B

Marks - 45

Answer any five questions.

4. (a) State Bohrs explanation of atomic structure.

(b) What are the properties of semiconductors ?

(c) Explain the formation of p type semiconductor.
3+3+3=9

5. (a) Explain how a crystal diode can work as a half wave rectifier.

(b) Derive an expression for the efficiency of a full wave rectifier.

(c) Define Ripple factor and derive an expression for it.
3+3+3=9

38/Et-305/AE-1 (5) [Turn over

6. (a) Explain how a Zener diode can work as a voltage regulator.
- (b) Draw the input and output characteristics for a common emitter configuration.
- (c) What is transistor load line ? How can the operating point be determined ? $3+3+3=9$
7. (a) Describe the operation of a clipping circuit.
- (b) Explain the construction and working of a RC coupled amplifier.
- (c) What do you understand by Class A, B, and Class C amplifiers ? $3+3+3=9$
8. (a) What is FET ? Explain its working principle.
- (b) State the differences between voltage and power amplifiers.
- (c) What do you understand by crossover distortion in a push pull amplifier ? $3+3+3=9$

9. Write short notes on any *three* : $3 \times 3 = 9$
 - (a) Photovoltaic cell
 - (b) Capacitor input filter
 - (c) Push pull amplifiers
 - (d) Base bias
 - (e) UJT.